

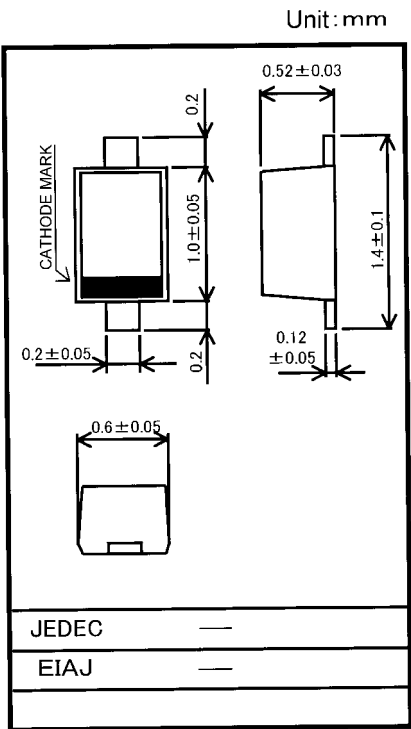
DIODE Silicon Epitaxial Planar Type

VCO for UHF Band Radio

- High Capacitance Ratio: $C_{0.5V}/C_{2.5V} = 2.5$ (typ.)
- Low Series Resistance : $r_s = 0.35\ \Omega$ (typ.)
- This device is suitable for use in a small-size tuner.

Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Reverse voltage	V_R	10	V
Junction temperature	T_j	150	°C
Storage temperature range	T_{stg}	-55~150	°C



Electrical Characteristics (Ta = 25°C)

Weight: 0.0011 g

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Reverse voltage	V_R	$I_R = 1\ \mu A$	10	—	—	V
Reverse current	I_R	$V_R = 10\ V$	—	—	3	nA
Capacitance	$C_{0.5V}$	$V_R = 0.5\ V, f = 1\ MHz$	7.3	—	8.4	pF
	$C_{2.5V}$	$V_R = 2.5\ V, f = 1\ MHz$	2.75	—	3.4	
Capacitance ratio	$C_{0.5V}/C_{2.5V}$	—	2.4	2.5	—	—
Series resistance	r_s	$V_R = 1\ V, f = 470\ MHz$	—	0.35	0.5	Ω

Note: Signal level when capacitance is measured: $V_{sig} = 500\ mV_{rms}$

Marking



